

SS12 THRU SS110

Features

Schottky Barrier Rectifier
Guard Ring Protection
Low Forward Voltage
Reverse Energy Tested
High Current Capability
Extremely Low Thermal Resistance

Maximum Ratings

Operating Temperature: -55 C to +125 C

Storage Temperature: -55 C to +150 C

Maximum Thermal Resistance; 35 C/W Junction To Lead

GM Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
SS12	SS12	20V	14V	20V
SS13	SS13	30V	21V	30V
SS14	SS14	40V	28V	40V
SS15	SS15	50V	35V	50V
SS16	SS16	60V	42V	60V
SS18	SS18	80V	56V	80V
SS110	SS110	100V	70V	100V

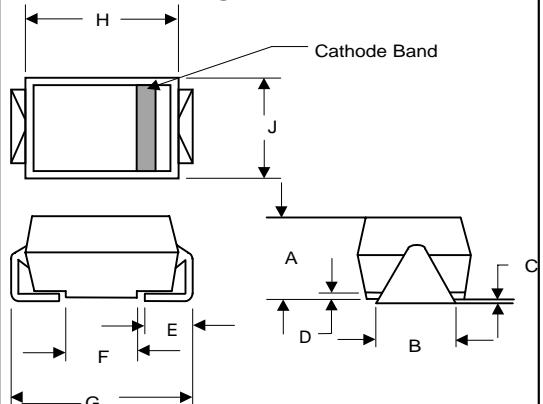
Electrical Characteristics @ 25 C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	1.0A	$T_J = 100$ C
Peak Forward Surge Current	I_{FSM}	30A	8.3ms, half sine
Maximum Instantaneous Forward Voltage			
SS12	V_F	.45V	$I_{FM} = 1.0A;$ $T_J = 25$ C*
SS13		.55V	
SS14		.60V	
SS15-16		.70V	
SS18-110		.85V	
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	0.5mA 20mA	$T_A = 25$ C $T_A = 100$ C
Typical Junction Capacitance			
SS18-SS110		20pF	1.0MHz, $V_R=4.0V$

*Pulse test: Pulse width 300 sec, Duty cycle 2%

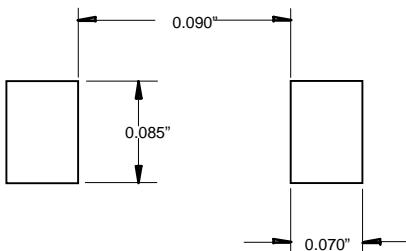
1 Amp Schottky Rectifier 20 to 100 Volts

DO-214AC (SMAJ) (High Profile)



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.078	.116	1.98	2.95	
B	.067	.089	1.70	2.25	
C	.002	.008	.05	.20	
D	---	.02	---	.51	
E	.035	.055	.89	1.40	
F	.065	.096	1.65	2.45	
G	.205	.224	5.21	5.69	
H	.160	.180	4.06	4.57	
J	.100	.112	2.57	2.84	

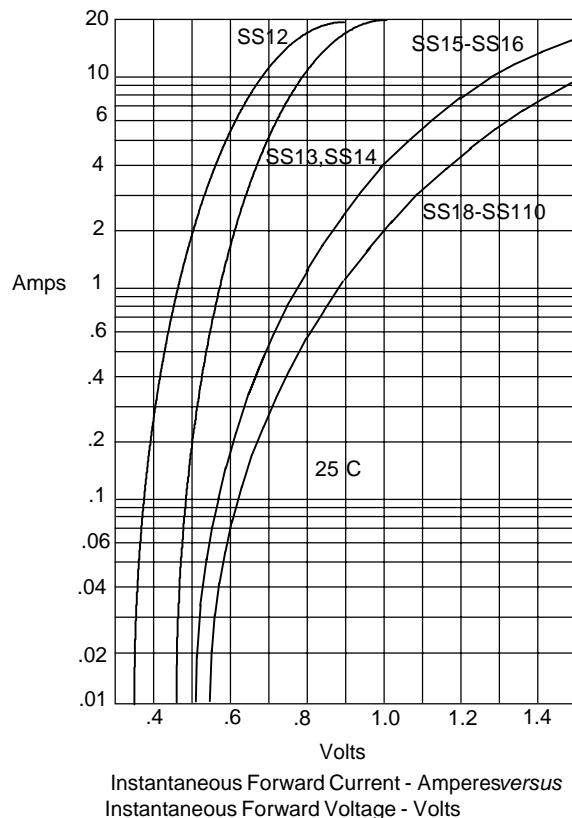
SUGGESTED SOLDER PAD LAYOUT



SS12 thru SS110

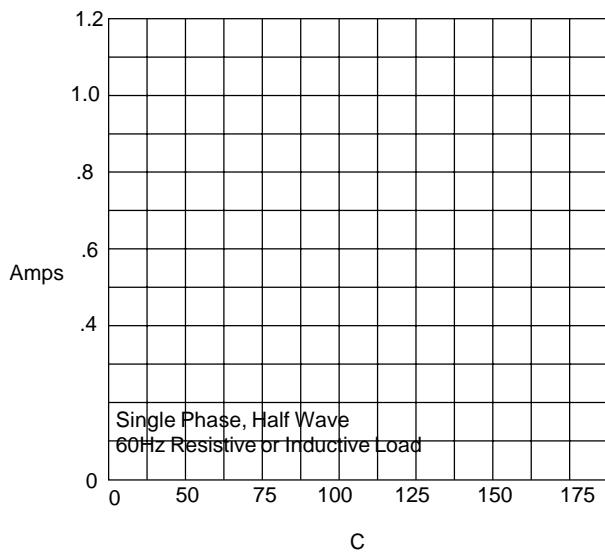
GM GarboMicro
Semiconductor

Figure 1
Typical Forward Characteristics



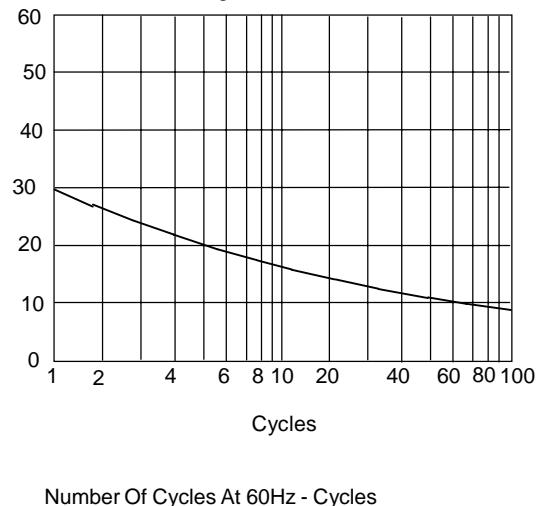
Instantaneous Forward Current - Amperes versus
Instantaneous Forward Voltage - Volts

Figure 2
Forward Derating Curve



Average Forward Rectified Current - Amperes versus
Ambient Temperature - C

Figure 3
Peak Forward Surge Current



Number Of Cycles At 60Hz - Cycles